

M.Sc. ELECTRONICS
SECOND SEMESTER
IC TECHNOLOGY & ANALOG ELECTRONIC CIRCUITS
MSE - 203

(Use Separate Answer Scripts for Objective & Descriptive)

Duration : 3 hrs.

Full Marks : 70

[**PART-A : Objective**]

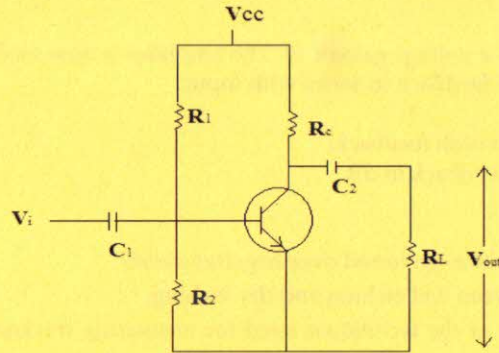
Time : 20 min.

Marks : 20

Choose the correct answer from the following:

1 × 20 = 20

6. a. With neat labeled diagram, describe the setup and process of Ion Milling in detail. 7+3=10
b. List the advantages and disadvantages of Ion Milling.
7. For the CE transistor amplifier circuit given in the figure below, $V_{CC} = 20$ V, $R_C = 20$ K Ω , $R_L = 2$ M Ω , $R_1 = 10$ K Ω , $R_2 = 10$ K Ω , $\beta = 100$. Find the r_e model and (i) R_{in} (ii) r_L (iii) A_i (iv) A_v (v) A_p & G_p 10



8. Derive the relation of frequency of oscillation and the feedback attenuation required for sustained oscillations for a Colpitt's oscillator. 10

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1. An amplifier has a power gain of 200. What is its gain in dB?
 - a. 14 dB
 - b. 23 dB
 - c. 22 dB
 - d. 17 dB
2. What are the types of MOSFET devices available?
 - a. P-type enhancement type MOSFET
 - b. N-type enhancement type MOSFET
 - c. Depletion type MOSFET
 - d. All of the mentioned
3. Which is the most striking feature in monolithic integrated circuit transistor?
 - a. Collector contact is present at the bottom of IC
 - b. Collector contact is present at the top of IC
 - c. Collector contact is absent
 - d. Collector contact is present on one of the sides of IC
4. Which of the following is used to obtain silicon crystal structure while fabricating Integrating Circuits?
 - a. Oxidation
 - b. Epitaxial growth
 - c. Photolithography
 - d. Silicon wafer preparations
5. Why oxidation process is required?
 - a. To protect against contamination
 - b. To use it for fabrication various components
 - c. To prevent diffusion of impurities
 - d. All of the mentioned
6. Where does the operating point of a Class A power amplifier lie?
 - a. At the middle of ac load line
 - b. Approximately at collector cut-off on both the dc and ac load lines
 - c. Inside the collector cut-off region on ac load line
 - d. At the middle of dc load line
7. The active components of the IC's are formed in
 - a. Substrate
 - b. SiO₂ layer
 - c. Epitaxial layer
 - d. None of these
8. Ultraviolet radiation is used in IC fabrication for
 - a. Diffusion
 - b. Masking
 - c. Isolation
 - d. Etching

